TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA8053H

3A DC MOTOR DRIVER WITH DIAGNOSIS

The TA8053H is a bidirectional DC motor driver with a current capacity of 3A. Inputs DI1 and DI2 are combined to select one of forward, reverse, stop, and brake modes.

The inputs are TTL-compatible, and separate power supplies are provided for the logic and output sections. The IC also incorporates various protective functions as well as a self-diagnostic function for diagnostic output

FEATURES

Output current capacity : 3A (Max.)
 Small standby current consumption : 100µA (Max.)

• Four operation modes : Forward, reverse, stop,

and brake

• Multiple protective functions : Short-circuit protection, thermal shutdown, and over-voltage shutdown

Self-diagnostic output
 On short-circuit detection

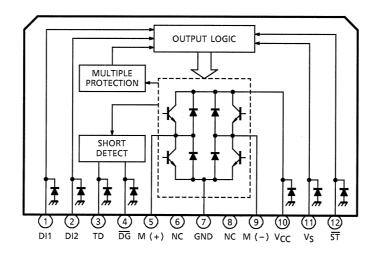
• Built-in counter electromotive force absorption diodes.

• Plastic package HZIP-12pin

HZIP12-P-1.78B

Weight: 4.0 g (Typ.)

BLOCK DIAGRAM AND PIN LAYOUT



PIN DESCRIPTION

PIN No.	SYMBOL	DESCRIPTION			
1 2	DI1 DI2	Output status control pin. Connects to a PNP-type voltage comparator.			
3	TD	$\overline{\text{Del}}$ ays the $\overline{\text{DG}}$ output. A capacitor is placed between this pin and GND.When the pin is open, $\overline{\text{DG}}$ is in switching state.			
4	DG	Self-diagnostic output pin. When the output current increases above 6A (typically), a switching waveform is output from this pin as from M (+) and M (–). If a capacitor is connected to the TD pin, the signal from this pin will go low after a certain delay. The output is an open-collector output. The delay time is approximately calculated by the following formula : $T_D (\text{ms}) = 50 \times C_T (\mu F) \\ \text{Permissible } C_T \text{range} : 0.01 \mu F \text{ to } 2 \mu F$			
5	M (+)	Connects to the DC motor. Both the sink and the source have a current capacity of 3A. Diodes for absorbing counter electromotive force are contained on the V _{CC} and GND sides.			
7	GND	Grounded			
9	M (-)	Connects to the DC motor together with pin 5 and has the same function as pin 5. This pin is controlled by the inputs from pins 1 and 2.			
10	V _{CC}	Power supply pin for the output section			
11	V _S	Power supply pin for the control section. This pin is completely separated from the V _{CC} pin.			
12	ST	When this pin is opened or grounded, the output turns off to reduce the current consumption below 100 μ A. If standby mode is not needed, the pin is connected to V _{CC} .			
6, 8	NC	Not connected. (Electrically, this pin is completely open.)			

TRUTH TABLE

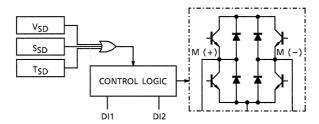
INPUT			OUTPUT	OUTPUT MODE		
DI1	DI2	ST	M (+)	M (-)	OUTPUT MODE	
Н	Н	Н	L	L	BRAKE	
L	Н	Н	L	Н	REVERSE	
Н	L	Н	Н	L	FORWARD	
L	L	Н	OFF (high impedance)		STOP	
H/L	H/L	L	OFF (high i	impedance)	STANDBY	

DESCRIPTION OF MULTI-PROTECTIVE OPERATION

The TA8053H has functions for protection from over-voltage (VSD), over-current (ISD), and overheat (TSD). These functions protect the IC (and the motor load in some cases) from deterioration or destruction due to power-related overstress.

The three functions work independently.

Each function is explained below.



1. Overvoltage protection (V_{SD})

· Basic operation

When the voltage supplied to the $V_{\rm CC}$ pin is up to the $V_{\rm SD}$ detection voltage, the output is controlled by the input signals. However, when the $V_{\rm CC}$ voltage exceeds the detection voltage, the output enters high-impedance state regardless of the input signals.

• Detailed explanation

The V_{SD} voltage is detected by comparing the reference voltage which is constructed by zenner diode. When the center voltage of the resistor is higher than the Zener voltage, a transistor-off instruction is issued to the control logic. When it is lower than the Zener voltage, the logic is controlled by the input signals from pins 1 and 2.

2. Overheat protection (T_{SD})

Basic operation

When the junction (chip) temperature is up to the TSD detection temperature, the output is controlled by the input signals. When it exceeds the TSD detection temperature, the output enters high-impedance state regardless of the input signals.

· Detailed explanation

The temperature is detected by monitoring VBE of a transistor on the chip. When the transistor VBE is lower than the internal reference voltage, an output transistor-off instruction is issued to the control logic. When it is higher than the internal reference voltage, the logic is controlled by the input signals from pins 1 and 2.

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3. Overcurrent protections (ISD)

· Basic operation

When the output current (pin 5 or 9, I sink or I source) is up to the ISD detection current, the output is controlled by the input signals. When it exceeds the detection current, the output assumes a switching waveform as shown in Fig.1.

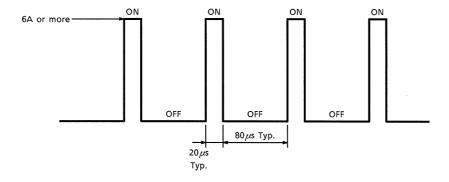


Fig.1 Basic Operation

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· Detailed explanation

The output current is detected by monitoring the VBE from each output transistor. One detection circuit connects to one of the output transistors and leads to the short-circuit protection circuit. When a current exceeding the ISD detection current flows through one of the four output transistors, the short-circuit protection circuit is activated. This circuit contains a timer. When over-current condition continues for 20µs (typically), the protection circuit places the output in high-impedance mode and, 80µs (typically) later, returns the IC to ON mode. The switching-waveform output is repeated until over-current condition is no longer present.

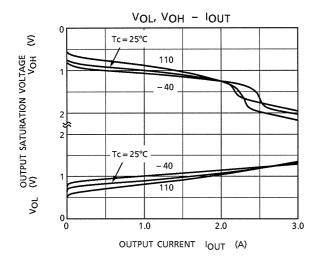
MAXIMUM RATINGS (Ta = 25°C)

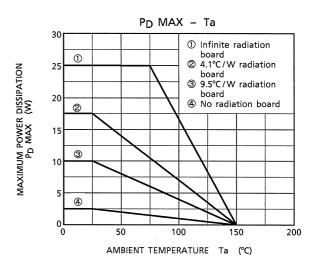
CHARACTERISTIC	SYMBOL	RATING	UNIT	
Power Supply Voltage	V _{CC}	30	V	
Power Supply Voltage	V _{CC}	60 (1s)		
Input Voltage	V _{IN}	-0.3~V _{CC}	V	
Output Current	I _{O AVE}	3.0	Α	
Operation Temperature	T _{opr}	-40~110	°C	
Storage Temperature	T _{stg}	-55~150	°C	
Power Dissipation	P_{D}	25	W	
Lead Temperature Time	T _{sol}	260 (10s)	°C	

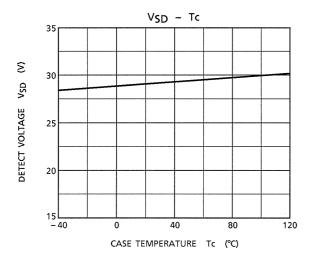
ELECTRICAL CHARACTERISTICS ($V_{CC} = 6 \sim 16V$, $T_C = -40 \sim 110$ °C)

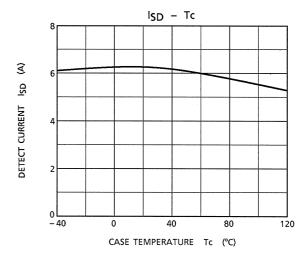
CHARACTERISTIC	SYMBOL	PIN	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
	I _{S1}	V _S	_	Stop	_	8	14	mA
Current Consumption (I)	I _{S2}		_	Forward / Reverse	_	22	42	
	I _{S3}		_	Brake	_	22	42	
	I _{CC1}	V _{CC}	_	Stop	_	5	8	mA
Current Consumption (II)	I _{CC2}		_	Forward / Reverse	_	18	42	
	I _{CC3}		_	Brake	_	5	8	
Input Voltage	V _{IL}	DI1 / DI2	_	_	_	_	8.0	V
input voitage	V _{IH}		_	_	2.0	_	_	
Input Current	I _{IL}	DI1 / DI2	_	V _{IN} = 0.4	_	_	-50	μΑ
input Guirent	I _{IH}	DITTOIL	_	V _{IN} = V _{CC}	_	_	10	
Input Voltage	V _{IL}	ST	_	_	_	_	0.8	V
input voltage	V _{IH}	31	_	_	2.0	_	_	
Input Current	I _{IL}	ST	_	V _{IN} = 0.4	_	_	50	μA
input Guirent	I _{IH}		_	V _{IN} = V _{CC}	_	_	4	mA
Output Saturation Voltage	V _{sat} (total)	M (+) / M (-)	_	I _O = 1.5A	1.0	2.1	2.8	V
Output Saturation Voltage	v _{sat} (total)		_	I _O = 3.0A	2.0	3.3	4.1	
Output Leakage Current	I _{LEAK-U}	M (+)/	_	V _O = 0V	_	_	-100	μΑ
Output Leakage Current	I _{LEAK-L}	M (-)	_	$V_O = V_{CC}$	_	_	100	
Output Voltage	V _{OL}	OL DG	_	I _{OL} = 3mA	_	_	0.5	V
Output Leakage Current	I _{LEAK-L}	DG	_	V _{OUT} = V _{CC}	_	_	10	μA
Diode Forward Voltage	V _{F-U}	M (+) / M (-)	_	I _F = 3.0A	_	5.0	_	V
Didde i di ward voltage	V _{F-L}		_	I _F = 3.0A	_	1.5	_	
Overcurrent Detection	I _{SD}	_	_	_	4.2	6	8	Α
Shutdown Temperature	T _{SD}	_	_		_	150	_	°C
Overvoltage Detection	V _{SD}				26	29	32	V
Standby Current	IS	V _{CC} +V _S	_	ST = GND			100	μA
Thermal Resistance	Rθ _{j-c}	_	_	_	_	3	_	°C/W
Transfer Delay Time	t _{pLH}	_	_	_	_	1	10	
Transier Delay Time	t _{pHL}	_	_	_		1	10	μs

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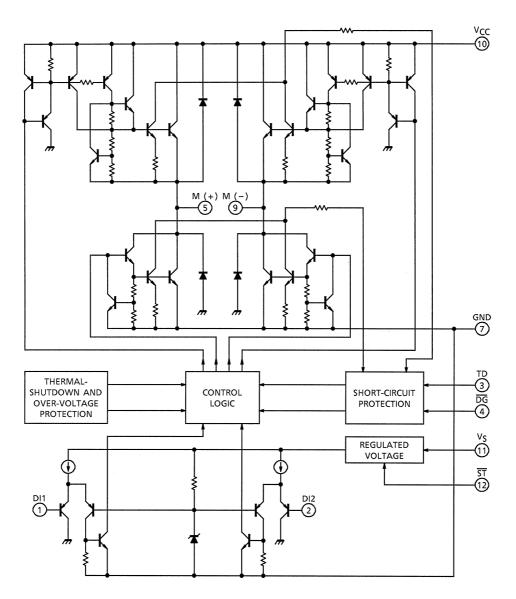




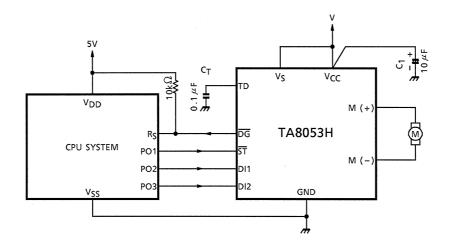


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I / O EQUIVALENT CIRCUIT



EXAMPLE OF APPLICATION CIRCUIT



(*): Cautions for wiring

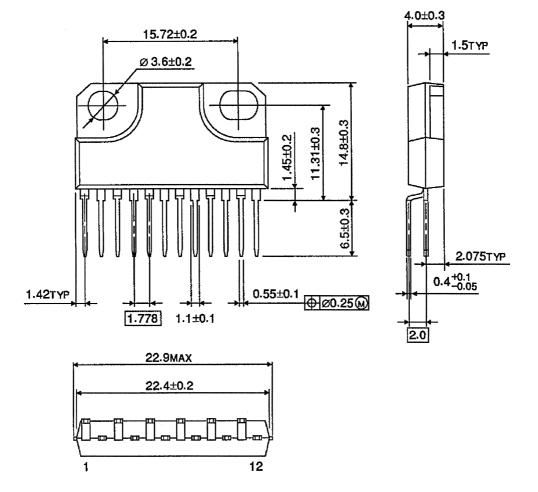
 $\ensuremath{C_1}$ is for absorbing disturbance noise, etc.

So, connect it as close as possible.

Package Dimensions

HZIP12-P- 1.78B

Unit: mm



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Weight: 4.0 g (Typ.)

2002-01-30

RESTRICTIONS ON PRODUCT USE

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